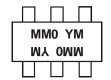


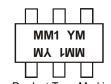
NOT RECOMMENDED FOR NEW DESIGN **USE DMN65D8LDW**

2N7002DWA

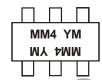
Marking Information



MM0 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017)M = Month (ex: 9 = September)



MM1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017)M = Month (ex: 9 = September)



MM4 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2012	-	20	17	2018	2019	2020	2021	20	22 2023	2024
Code	Z	-		E	F	G	Н	I	J	J K	L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct N	ov Dec
Code	1	2	3	4	5	6	7	8	9	0 1	N D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Characteristic			Symbol	Value	Unit
Drain-Source Voltage				V _{DSS}	60	V
Gate-Source Voltage				V _{GSS}	±20	V
Continuous Drain Current (Note 5)	V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	180 140	mA
Continuous Drain Current (Note 5)	V _{GS} = 5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	۵ا	150 120	mA
Continuous Drain Current (Note 6)	V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	200 160	mA
Continuous Drain Current (Note 6)	V _{GS} = 5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	170 140	mA
Pulsed Drain Current (10µs Pulse, D	uty Cycle = 1%)			I _{DM}	700	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	435	°C/W
Total Power Dissipation (Note 6)	P_{D}	400	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ hetaJA}$	330	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	139	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

NOT RECOMMENDED FOR NEW DESIGN USE DMN65D8LDW

2N7002DWA

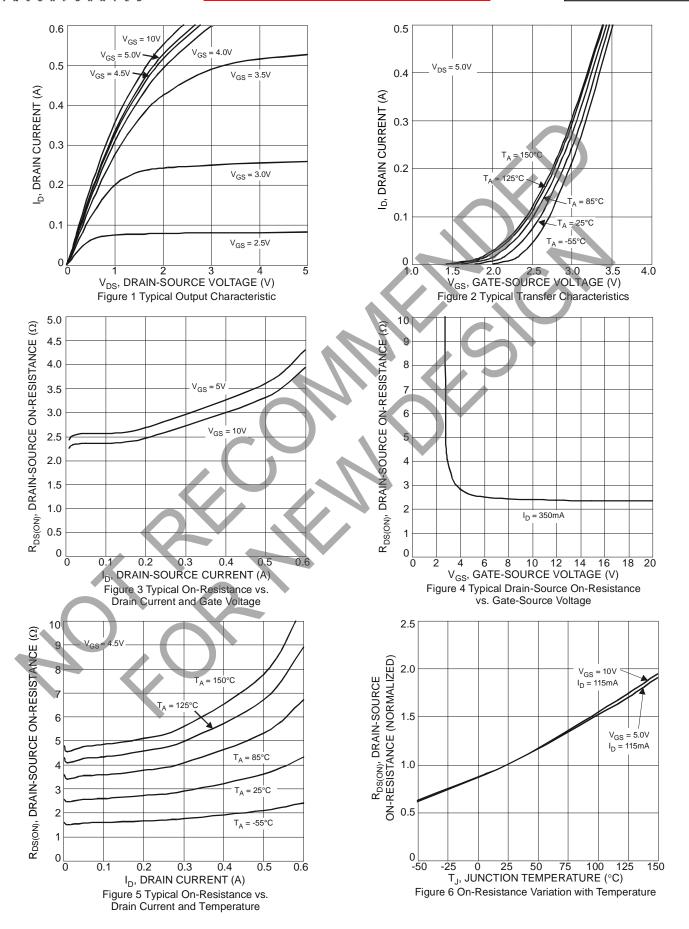
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	I	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	1	_	±5	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.8	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance				8	Ω	$V_{GS} = 5.0V, I_D = 0.115A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	1	_	6	Ω	$V_{GS} = 10.0 V, I_D = 0.115 A$	
Forward Transconductance	g FS	80	_	_	mS	$V_{DS} = 10V, I_D = 0.115A$	
Diode Forward Voltage	V_{SD}		0.8	1.2	٧	$V_{GS} = 0V, I_S = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	I	22.0	_			
Output Capacitance	Coss	1	3.2	1	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_	2.0	1			
Gate Resistance	R_{G}		88	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge V _{GS} = 10V	Q_g	1	0.87	1			
Total Gate Charge V _{GS} = 4.5V	Q_{g}	_	0.43	M	nC	$V_{GS} = 10V, V_{DS} = 30V,$	
Gate-Source Charge	Q _{gs}		0.11			$I_D = 150 \text{mA}$	
Gate-Drain Charge	Q_{gd}	1	0.11	_			
Turn-On Delay Time	t _{D(ON)}	1	3.3	(
Turn-On Rise Time	t _R		3.2		nc	$V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}		12.0		ns	$R_{GEN} = 25\Omega$	
Turn-Off Fall Time	t _F		6.3				

Notes:

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

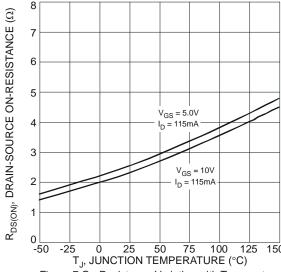


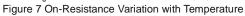


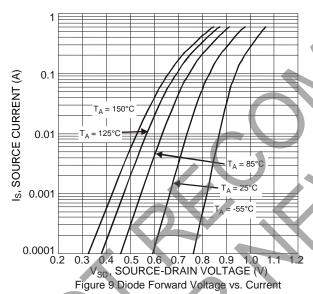


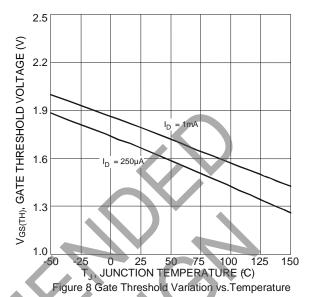
NOT RECOMMENDED FOR NEW DESIGN USE DMN65D8LDW

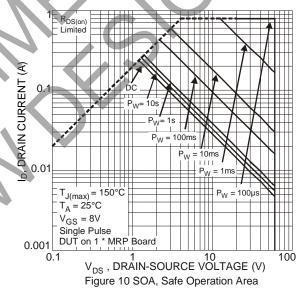
2N7002DWA







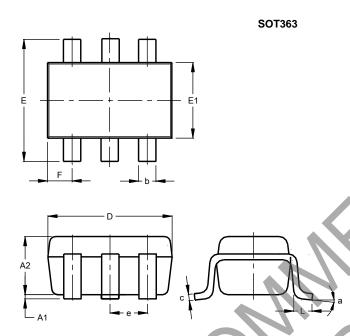






Package Outline Dimensions

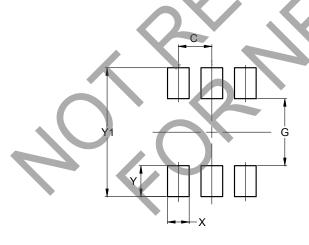
Please see http://www.diodes.com/package-outlines.html for the latest version.



		_						
SOT363								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	1.00					
b	0.10	0.30	0.25					
C	0.10	0.22	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	0.650 BSC							
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
Х	0.420		
Y	0.600		
V1	2 500		

SOT363



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